# 2SB1418, 2SB1418A

## Silicon PNP epitaxial planar type darlington

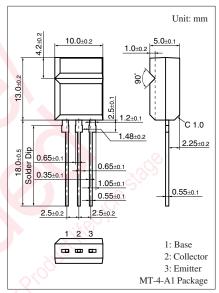
For power amplification
Complementary to 2SD2138 and 2SD2138A

#### ■ Features

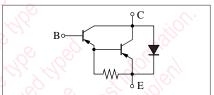
- High forward current transfer ratio hFE
- High-speed switching
- Allowing automatic insertion with radial taping

### ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage	2SB1418	V <sub>CBO</sub>	-60	V
(Emitter open)	2SB1418A		-80	
Collector-emitter voltage	2SB1418	V <sub>CEO</sub>	-60	V
(Base open)	2SB1418A		-80	
Emitter-base voltage (Coll	V <sub>EBO</sub>	-5	V	
Collector current	$I_{\rm C}$	-2	A	
Peak collector current	$I_{CP}$	-4	A	
Collector power dissipation	P <sub>C</sub>	15	W	
	$T_a = 25^{\circ}C$		2.0	
Junction temperature	$T_{j}$	150	°C	
Storage temperature	$T_{stg}$	-55 to +150	S°C	



#### Internal Connection



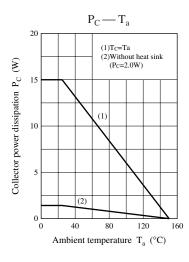
### ■ Electrical Characteristics $T_C = 25$ °C $\pm 3$ °C

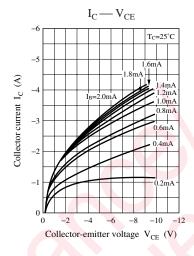
Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage	2SB1418	$V_{CEO}$	$I_C = -30 \text{ mA}, I_B = 0$	-60	0,		V
(Base open)	2SB1418A		6. 1. 90. 04.07	-80	0		
Base-emitter voltage	ies	$V_{ m BE}$	$V_{CE} = -4 \text{ V}, I_{C} = -2 \text{ A}$	160		-2.8	V
Collector-base cutoff	2SB1418	$I_{CBO}$	$V_{CB} = -60 \text{ V}, I_E = 0$			-100	μΑ
current (Emitter open)	2SB1418A		$V_{CB} = -80 \text{ V}, I_{E} = 0$			-100	
Collector-emitter cutoff	2SB1418	$I_{CEO}$	$V_{CE} = -30 \text{ V}, I_B = 0$			-100	μΑ
current (Base open)	2SB1418A		$V_{CE} = -40 \text{ V}, I_{B} = 0$			-100	
Emitter-base cutoff current (Collector open)		$I_{EBO}$	$V_{EB} = -5 \text{ V}, I_C = 0$			-100	μΑ
Forward current transfer ratio		h <sub>FE1</sub>	$V_{CE} = -4 \text{ V}, I_{C} = -1 \text{ A}$	1000			_
		h <sub>FE2</sub> *	$V_{CE} = -4 \text{ V}, I_{C} = -2 \text{ A}$	1000		10 000	
Collector-emitter saturation voltage		V <sub>CE(sat)</sub>	$I_C = -2 \text{ A}, I_B = -8 \text{ mA}$			-2.5	V
Transition frequency		$f_T$	$V_{CE} = -10 \text{ V}, I_{C} = -0.5 \text{ A}, f = 1 \text{ MHz}$		20		MHz
Turn-on time		t <sub>on</sub>	$I_C = -2 \text{ A}, I_{B1} = -8 \text{ mA}, I_{B2} = 8 \text{ mA}$		0.2		μs
Turn-off time		$t_{\rm off}$	$V_{CC} = -50 \text{ V}$		2		μs

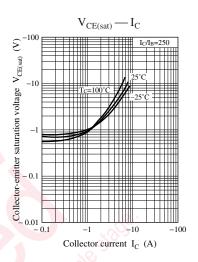
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

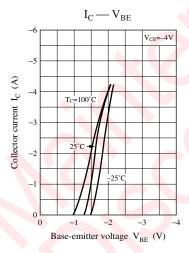
#### 2. \*: Rank classification

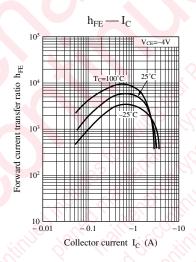
Rank	R	Q	Р
h <sub>FE2</sub>	1000 to 2500	2000 to 5000	4000 to 10000

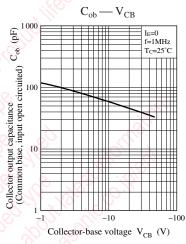


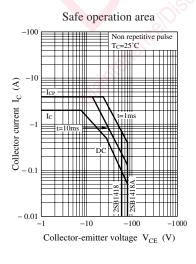


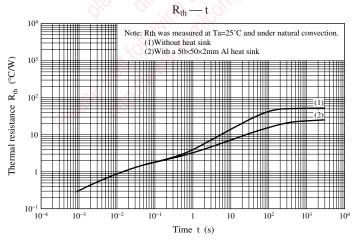












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